

Substitute for form 1449A/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet 11

of 2

Attorney Docket Number

84.355

Complete if Known

Application Number	10/693,847
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10/693,847

Filing Date	10/20/03
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10/20/03

First Named Inventor	August et al.
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August et al.

Group Art Unit	:	Not Yet Assigned
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Not Yet Assigned

Examiner Name	Not Yet Assigned
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Not Yet Assigned

Attorney Docket Number

84.355

U.S. PATENT DOCUMENTS

[illegible]

FOREIGN PATENT DOCUMENTS

[illegible]

**Examiner
Signature**

Date:

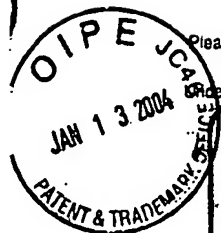
Considered

18/6/05

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Substitute for form 1449B/PTO		Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Application Number	10/693,847
		Filing Date	10/20/03
		First Named Inventor	August et al.
		Group Art Unit	Not Yet Assigned
		Examiner Name	Not Yet Assigned
Sheet 2 of 2	Attorney Docket Number	84,355	

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS); title of the article (when appropriate); title of the item (book, magazine, journal, serial, symposium, catalog, etc.); date, page(s), volume-issue number(s), publisher, city and/or country where published.	7
DR		MCGREGOR et al, "Self-Biased Boron-10 Coated High-Purity Epitaxial GaAs Thermal Neutron Detector" IEEE transactions on nuclear science, vol. 47, no., August 2000	
DR		MCGREGOR et al, "Recent Results From Thin-Film-Coated Semiconductor Neutron Detectors" X-Ray and Gamma-Ray Detector and Application IV, vol. 4784 (2002).	
DR		HAQUE et al, "Neutron dosimetry employing soft errors in dynamic random access memories" Phys. Med. Biol., 1989 vol. 34, no 9, 1195-1202 Printed in the UK	
DR		PHILLIPS et al, "Feasibility of a Neutron Detector-Dosimeter Based on Single-Event Upsets in Dynamic Random-Access Memories" Radiation Protection Dosimetry vol. 101, nos. 1-4, pp. 129-132 (2002) Nuclear Technology Publishing	
DR		ROBERTSON et al, "A class of boron-rich solid-state neutron detectors" Applied Physics Letters volume 80, number 19, 13 May 2002	
DR		GUARINI et al, "Electrical Integrity of State-of-the-Art 0.13 um SOI-CMOS Devices and Circuits Transferred for Three-Dimensional (3D) Integrated Circuit (IC) Fabrication" 0-7803-7462-2/02 2002 IEEE	
DR		ARITA et al, "Experimental Investigation of Thermal Neutron-Induced Single Event Upset in Static Random Access Memories" Jpn. J. Appl. Phys Vol. 40 (2001) pp. L151-L153 Part 2, No. 2B, 15 February 2001	
DR		HUGHES et al, "Radiation Effects and Hardening of Mos Technology: Devices and Circuits" Preprint IEEE Trans. Nucl. Sci. June 2003	
DR		LUND et al, "Neutron Dosimeter Using a Dynamic Random Access Memory as a Sensor" IEEE Transactions on Nuclear Science, Vol. 33, No. 1, February 1996	
DR		PETERSEN et al, "Calculation of Cosmic-Ray Induced Soft Upsets and Scaling in VLSI Devices*" IEEE Transaction on Nuclear Science, Vol. NS-29, No. 6, December 1982	
DR		DAVIS "Use of Computer Memory Chips as The Basis For a Digital Albedo Neutron Dosimeter*" Health Physics Vol. 49, No. 2 (August), pp. 259-265, 1985 Printed in the U.S.A.	

Examiner Signature		Date Considered	10/6/05
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